

Attny. Docket No.: 2003-0395/N1085-90166

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

1 -8(Cancelled)

9.(Currently Amended) The method of claim 1 ~~29~~ wherein the flowing and generating steps (b) to (d) are performed in a CVD process chamber.

10.(Currently Amended) The method of claim 1 ~~29~~ wherein the deposition rate of said carbon doped SiO₂ film is from about 5000 to 8000 Angstroms per minute.

11-28 (Cancelled)

29.(New) A method of depositing a carbon doped SiO₂ film on a substrate, the method comprising the steps of:

flowing oxygen, argon, and an organosilane selected from the group consisting of dimethylsilane, trimethylsilane, and tetramethylsilane, over the substrate at a flow rate ratio of about 1:1.5:6; and

generating a plasma to deposit the carbon doped SiO₂ film on the substrate.

30.(New) The method of claim 29 wherein the organosilane comprises the tetramethylsilane.

31.(New) The method of claim 30 wherein the flowing of the oxygen is performed at a flow rate of from about 50 to 300 sccm, the flowing of the tetramethylsilane is performed at a flow rate of between about 400 and 800 sccm, and the flowing of the argon is performed at a flow rate of between about 50 and 300 sccm.

32.(New) The method of claim 29 wherein the plasma generating step is performed at a temperature between about 300°C and 400°C, an RF power from about 600 to 800 Watts, and a pressure between about 1.5 and 4 Torr,

Attty. Docket No.: 2003-0395/N1083-90166

33.(New) The method of claim 29 wherein the carbon doped SiO₂ film is deposited to a thickness of about 4000 to 8000 Angstroms.

34.(New) A method of depositing a carbon doped SiO₂ film on a substrate, the method comprising the steps of:

flowing oxygen, argon, and an organosilane selected from the group consisting of dimethylsilane, trimethylsilane, and tetramethylsilane, over the substrate; and

generating a plasma to deposit the carbon doped SiO₂ film on the substrate,

wherein the deposition rate of the carbon doped SiO₂ film is from about 5000 to 8000 Angstroms per minute.